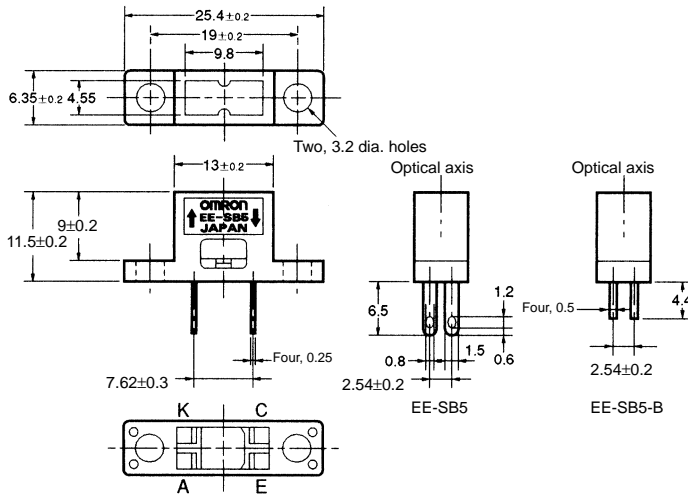


EE-SB5(-B)

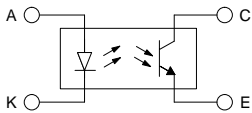
Photomicrosensor (Reflective)

■ Dimensions

Note: All units are in millimeters unless otherwise indicated.



Internal Circuit



Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance
3 mm max.	±0.3
3 < mm ≤ 6	±0.375
6 < mm ≤ 10	±0.45
10 < mm ≤ 18	±0.55
18 < mm ≤ 30	±0.65

Terminal No.	Name
A	Anode
K	Cathode
C	Collector
E	Emitter

■ Features

- Dust-tight construction.
- With a visible-light intercepting filter which allows objects to be sensed without being greatly influenced by the light radiated from fluorescent lamps.
- Mounted with M3 screws.
- Model with soldering terminals (EE-SB5).
- Model with PCB terminals (EE-SB5-B).

■ Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rated value
Emitter	Forward current	I _F 50 mA (see note 1)
	Pulse forward current	I _{FP} 1 A (see note 2)
	Reverse voltage	V _R 4 V
Detector	Collector-Emitter voltage	V _{CEO} 30 V
	Emitter-Collector voltage	V _{ECO} ---
	Collector current	I _C 20 mA
	Collector dissipation	P _C 100 mW (see note 1)
Ambient temperature	Operating	T _{opr} -25°C to 80°C
	Storage	T _{stg} -30°C to 80°C
Soldering temperature		T _{sol} 260°C (see note 3)

- Note:**
1. Refer to the temperature rating chart if the ambient temperature exceeds 25°C.
 2. The pulse width is 10 μs maximum with a frequency of 100 Hz.
 3. Complete soldering within 10 seconds.

■ Electrical and Optical Characteristics (Ta = 25°C)

Item	Symbol	Value	Condition
Emitter	Forward voltage	V _F 1.2 V typ., 1.5 V max.	I _F = 30 mA
	Reverse current	I _R 0.01 μA typ., 10 μA max.	V _R = 4 V
	Peak emission wavelength	λ _P 940 nm typ.	I _F = 20 mA
Detector	Light current	I _L 200 μA min., 2,000 μA max.	I _F = 20 mA, V _{CE} = 10 V White paper with a reflection ratio of 90%, d = 5 mm (see note)
	Dark current	I _D 2 nA typ., 200 nA max.	V _{CE} = 10 V, 0 lx
	Leakage current	I _{LEAK} 2 μA max.	I _F = 20 mA, V _{CE} = 10 V with no reflection
	Collector-Emitter saturated voltage	V _{CE (sat)}	---
	Peak spectral sensitivity wavelength	λ _P 850 nm typ.	V _{CE} = 10 V
Rising time	t _r	30 μs typ.	V _{CC} = 5 V, R _L = 1 kΩ, I _L = 1 mA
Falling time	t _f	30 μs typ.	V _{CC} = 5 V, R _L = 1 kΩ, I _L = 1 mA

Note: The letter "d" indicates the distance between the top surface of the sensor and the sensing object.